

CLAIM CHANGES:

1. Cancelled
2. Cancelled
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7. A method of manufacturing a semiconductor device comprising:
forming an element isolation region in a semiconductor substrate of a first conductivity type to partition an active area in the semiconductor substrate;
forming a semiconductor region of a second conductivity type in the active area;
etching the element isolation region to expose a side of the active area;
forming a metal layer at least on the active area after the side of the active area is exposed;
causing the metal layer to react on the active area to form a reaction layer of metal constituting the metal layer and a semiconductor constituting the active area;
and
removing an unreacted portion of the metal layer and leaving the reaction layer on a surface of the semiconductor region of the second conductivity type formed in the active area.
8. The method according to claim 7, wherein the semiconductor substrate is silicon, and the reaction layer is a silicide layer.